BUK7618-55

N-channel TrenchMOS standard level FET Rev. 2 — 26 April 2011

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Electrostatically robust due to integrated protection diodes
- Low conduction losses due to low on-state resistance

1.3 Applications

Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	T _{mb} = 25 °C	-	-	57	Α
P _{tot}	total power dissipation		-	-	125	W
Static char	racteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	15	18	mΩ
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 50 \text{ A; } V_{sup} \leq 25 \text{ V;} \\ R_{GS} &= 50 \Omega; V_{GS} = 10 \text{ V;} \\ T_{j(init)} &= 25 ^{\circ}\text{C; } unclamped \end{split}$	-	-	125	mJ



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

Ordering information

Table 3. **Ordering information**

Type number	Package		
	Name	Description	Version
BUK7618-55	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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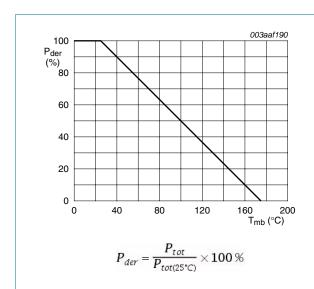
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Limiting values

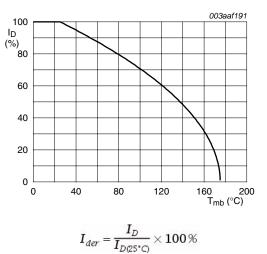
Limiting values Table 4.

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V_{GS}	gate-source voltage		-16	16	V
I _D	drain current	T _{mb} = 25 °C	-	57	Α
		T _{mb} = 100 °C	-	40	Α
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed	-	228	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	125	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	n diode				
Is	source current	T _{mb} = 25 °C	-	57	Α
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	200	Α
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 50 A; V_{sup} ≤ 25 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	125	mJ
Electrostation	c discharge				
V _{esd}	electrostatic discharge voltage	HBM; C = 100 pF; R = 1.5 k Ω ; (all pins)	-	2	kV



Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 5 \text{ V}$

Normalized continuous drain current as a function of mounting base temperature

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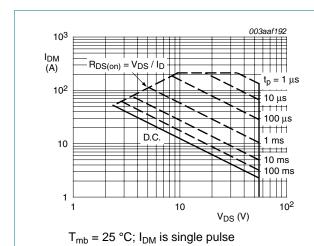


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

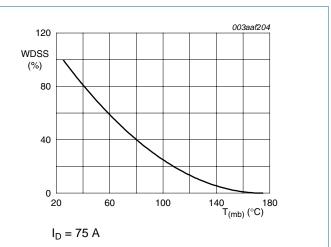


Fig 4. Normalised drain-source avalanche energy as a function of mounting-base temperature.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	50	-	K/W

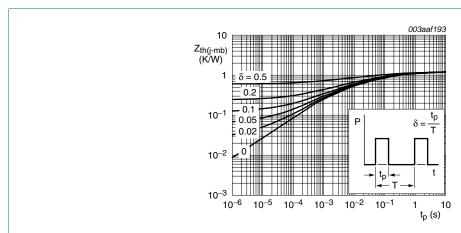


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

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6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS} drain-source		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
V _{GS(th)} gate-source threshold voltage	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	4.4	V
I _{DSS} drain leakage cui	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _i = 25 °C	-	0.02	1	μΑ
		$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_i = 175 \text{ °C}$	-	-	20	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _i = 175 °C	-	-	20	μΑ
200	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _i = 175 °C	-	-	38	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _i = 25 °C	-	15	18	mΩ
V _{(BR)GSS}	gate-source	$V_{DS} = 0 \text{ V; } T_i = 25 \text{ °C; } I_G = 1 \text{ mA}$	16	-	-	V
	breakdown voltage	$V_{DS} = 0 \text{ V}; T_i = 25 \text{ °C}; I_G = -1 \text{ mA}$	16	-	-	V
Dynamic	characteristics	,				
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1500	2000	pF
C _{oss}	output capacitance	T _j = 25 °C	-	370	470	pF
C _{rss}	reverse transfer capacitance		-	170	250	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	15	22	ns
t _r	rise time	$R_{G(ext)}$ = 10 Ω ; I_D = 25 A; T_j = 25 °C	-	30	60	ns
t _{d(off)}	turn-off delay time		-	35	50	ns
t _f	fall time		-	25	38	ns
L _D	internal drain inductance	measured from upper edge of drain mounting base to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nΗ
L _S	internal source inductance	measured from source lead soldering point to source bond pad; $T_j = 25$ °C	-	7.5	-	nΗ
g _{fs}	transfer conductance	$V_{DS} = 25 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	6	30	-	S
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 50 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	1	-	V
		$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.95	1.2	V
t _{rr}	reverse recovery time	$I_S = 50 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	48	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	0.1	-	μC

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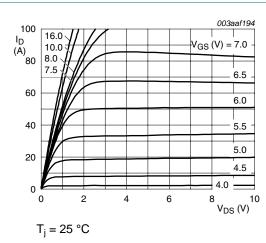


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

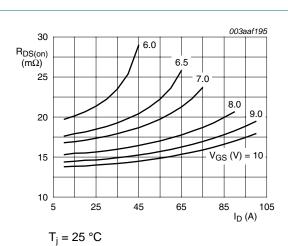


Fig 7. Drain-source on-state resistance as a function of drain current; typical values

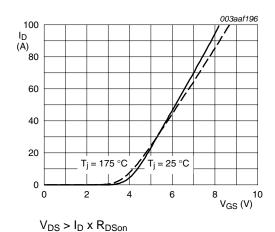


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

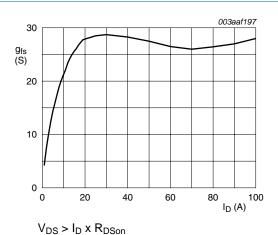


Fig 9. Forward transconductance as a function of drain current; typical values

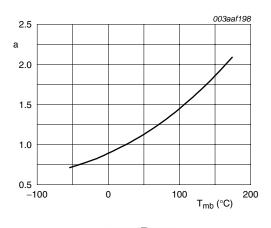


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

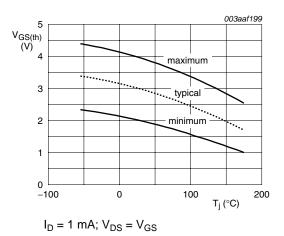


Fig 11. Gate-source threshold voltage as a function of junction temperature

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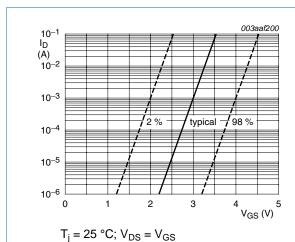
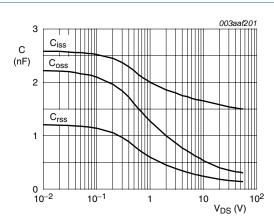
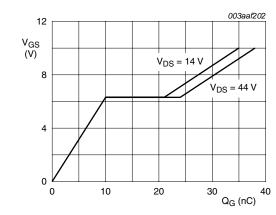


Fig 12. Sub-threshold drain current as a function of gate-source voltage



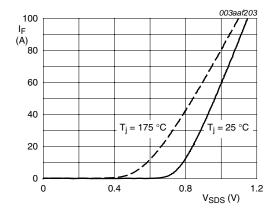
 $V_{GS} = 0 V$; f = 1 MHz

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C; I_D = 50 \, A$

Fig 14. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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7. Package outline

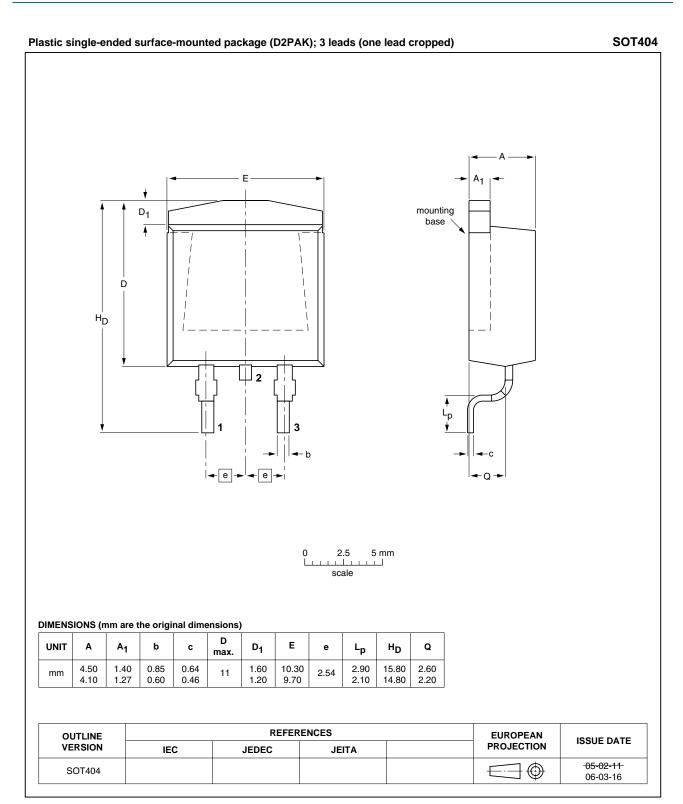


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7618-55 v.2	20110426	Product data sheet	-	BUK7618-55_1
Modifications:	 The format of of NXP. 	this data sheet has been red	lesigned to comply with	the new identity guidelines
	 Legal texts have 	ve been adapted to the new	company name where	appropriate.
BUK7618-55_1	19980401	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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